









SLVSE49B - JULY 2017 - REVISED AUGUST 2024

ESD401

ESD401 1-Channel ESD Protection Diode With Robust IEC ESD Performance

1 Features

- Robust IEC 61000-4-2 level 4 ESD protection:
 - ±24kV contact discharge
 - ±30kV air gap discharge
- IEC 61000-4-5 surge protection:
 - 4.5A (8/20µs)
 - Low V_{clamp} of 12V at 1.8A I_{PP} (8/20µs)
- IEC 61000-4-4 EFT protection:
 - 80A (5/50ns)
- Bi-directional ESD diode to protect interfaces up to
- IO capacitance: 0.77pF (typical)
- High DC breakdown voltage: 8.3V (typical)
- Ultra low leakage current: 30pA (typical)
- Low dynamic resistance 0.7Ω (typical)
- Industrial temperature range: -40°C to +125°C
- Industry standard 0402 package

2 Applications

- End equipment:
 - Wearables
 - Laptops and desktops
 - Mobile and tablets
 - Set-top boxes
 - **DVR** and **NVR**
 - TV and monitors
 - EPOS (electronic point of sale)
- Interfaces:
 - 1 Gbps ethernet
 - USB 2.0/1.1 with 5.5 V tolerance
 - **GPIO**
 - Pushbuttons/keypad
 - Audio

3 Description

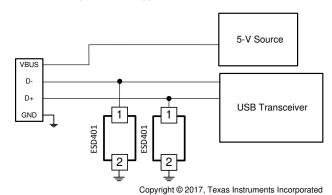
The ESD401 is a bidirectional TVS ESD protection diode featuring low R_{DYN} and low clamping voltage. The ESD401 is rated to dissipate ESD strikes exceeding the maximum level specified in the IEC 61000-4-2 international standard (Level 4). The low dynamic resistance (0.7Ω) to ensure system level protection against transient events. This device features a 0.77pF IO capacitance making it ideal for protecting interfaces such as USB 2.0. The device can operate with ultra-low leakage up to ±5.5V and survive DC faults up to 8.3V.

The ESD401 is offered in the industry standard 0402 (DPY) package.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
ESD401	DPY (X1SON, 2)	1mm × 0.6mm

- For more information, see Section 10.
- (2)The package size (length × width) is a nominal value and includes pins, where applicable.



Typical USB 2.0 Application Schematic



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4 Pin Configuration and Functions

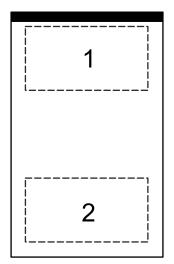


Figure 4-1. DPY Package, 2-Pin X1SON (Top View)

Table 4-1. Pin Functions

F	PIN	TYPE ⁽¹⁾ DESCRIPTION		
NAME	NO.	I I PE\''	DESCRIPTION	
Ю	1	I/O	ESD Protected Channel. If used as ESD IO, connect pin 2 to ground	
Ю	2	I/O	ESD Protected Channel. If used as ESD IO, connect pin 1 to ground	

(1) I = input, O = output



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Electrical fast transient	IEC 61000-4-4 (5/50 ns) at 25°C		80	А
Peak pulse	IEC 61000-4-5 power (t _p - 8/20 µs) at 25°C		67	W
	IEC 61000-4-5 current (t _p - 8/20 μs) at 25°C		4.5	А
T _A	Operating free-air temperature	-40	125	°C
T _{stg}	Storage temperature	-65	155	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD Ratings — JEDEC Specification

			VALUE	UNIT
\/	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2500	
V _(ESD)	Liectiostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 ESD Ratings—IEC Specification

			VALUE	UNIT
V	Electrostatic discharge	IEC 61000-4-2 contact discharge	±24000	V
V _(ESD)	Liectiostatic discharge	IEC 61000-4-2 air-gap discharge	±30000	

5.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	3 1 3 1		
		MIN M	AX UNIT
V _{IO}	Input pin voltage	-5.5	5.5 V
T _A	Operating free-air temperature	-40	25 °C

5.5 Thermal Information

		ESD401	
	THERMAL METRIC ⁽¹⁾	DPY (X1SON)	UNIT
		2 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	420	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	169.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	276.1	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	122.1	°C/W
ΨЈВ	Junction-to-board characterization parameter	157.3	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

Product Folder Links: ESD401



5.6 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{RWM}	Reverse stand-off voltage	I _{IO} < 10 nA	-5.5		5.5	V
V_{BRF}	Breakdown voltage, Pin 1 to Pin 2 (1)	I _{IO} =1 mA, at T _A = 25°C	7.5		9.1	V
V_{BRR}	Breakdown voltage, Pin 2 to Pin 1 (1)	I _{IO} =1 mA, at T _A = 25°C	7.5		9.1	V
V _{HOLD}	Holding voltage ⁽²⁾	I _{IO} =1 mA		8.3		V
		I _{PP} = 1 A, TLP, from Pin 1 to Pin 2 and Pin 2 to Pin 1, T _A = 25°C		11		
		I _{PP} = 5 A, TLP, from Pin 1 to Pin 2 and Pin 2 to Pin 1, T _A = 25°C		16	8.3	
V_{CLAMP}	Clamping voltage	I _{PP} = 16 A, TLP, from Pin 1 to Pin 2 and Pin 2 to Pin 1, T _A = 25°C		24		V
CLAIVIP	oramping relage	I _{PP} = 1.8 A, IEC-61000-4-5 (t _p - 8/20 μs) from Pin 1 to Pin 2 and Pin 2 to Pin 1, T _A = 25°C		12		·
		I _{PP} = 4.5 A, IEC-61000-4-5 (t _p - 8/20 μs) from Pin 1 to Pin 2 and Pin 2 to Pin 1, T _A = 25°C		15		
I _{LEAK}	Leakage current, Pin 1 to Pin2 and Pln2 to Pin 1	V _{IO} = ±2.5 V		0.03	10	nA
R _{DYN}	Dynamic resistance	Measured between TLP I _{PP} of 10 A and 20 A, Pin 2 to Pin 1 and Pin 1 to Pin2, T _A = 25°C		0.7		Ω
C _L	Line capacitance	V_{IO} = 0 V, f = 1 MHz, Pin 1 to Pin 2 and Pin2 to Pin1, T_A = 25°C		0.77	0.95	pF

⁽¹⁾ V_{BRF} and V_{BRR} are defined as the voltage obtained at 1 mA when sweeping the voltage up, before the device latches into the snapback state.

⁽²⁾ V_{HOLD} is defined as the voltage when 1 mA is applied, after the device has successfully latched into the snapback state.



5.7 Typical Characteristics

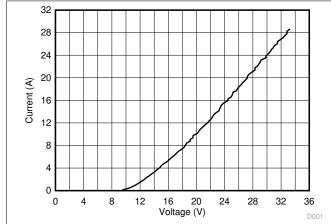


Figure 5-1. Positive TLP Curve, Pin 1 to Pin 2

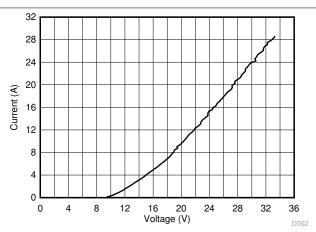


Figure 5-2. Negative TLP Curve, Pin 1 to Pin 2 (Plotted as Positive TLP Curve Pin 2 to Pin 1

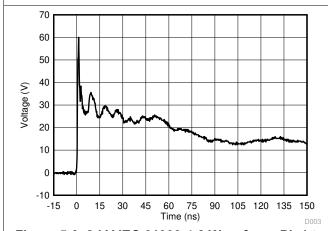


Figure 5-3. 8-kV IEC 61000-4-2 Waveform, Pin1 to Pin 2

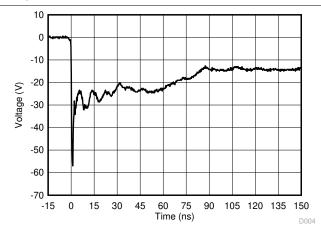


Figure 5-4. –8-kV IEC 61000-4-2 Waveform, Pin 1 to Pin 2

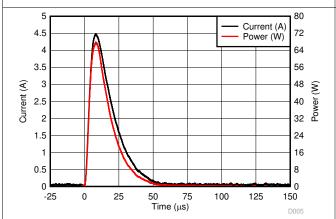


Figure 5-5. Surge (IEC 61000-4-5) Curve (tp = 8/20 µs), Pin 1 to Pin 2

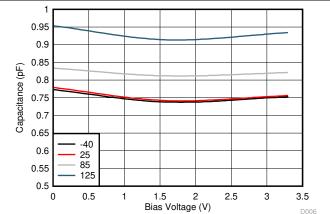


Figure 5-6. Capacitance vs Bias Voltage, Pin 1 to Pin 2

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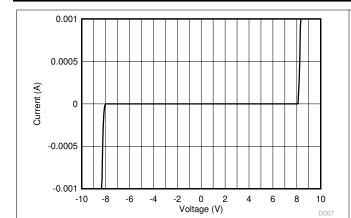


Figure 5-7. DC Voltage Sweep I-V Curve, Pin 1 to Pin 2

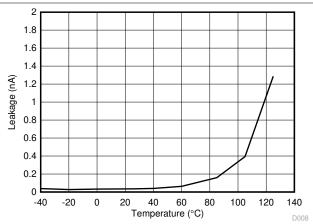


Figure 5-8. Leakage Current vs. Temperature, Pin 1 to Pin 2

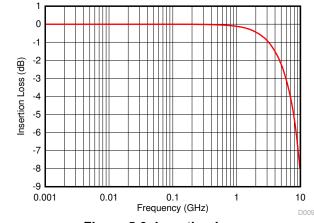


Figure 5-9. Insertion Loss

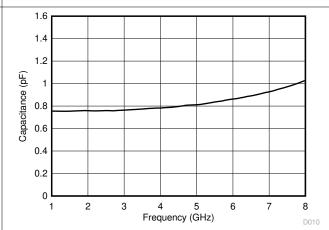


Figure 5-10. Capacitance vs. Frequency, Pin 1 to Pin 2



6 Detailed Description

6.1 Overview

The ESD401 is a bidirectional ESD Protection Diode with ultra-low clamping voltage. This device can dissipate ESD strikes above the maximum level specified by the IEC 61000-4-2 International Standard. The ultra-low clamping makes this device ideal for protecting any sensitive signal pins.

6.2 Functional Block Diagram



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6.3 Feature Description

6.3.1 IEC 61000-4-2 ESD Protection

The I/O pins can withstand ESD events up to ±24-kV contact and ±30-kV air gap. An ESD-surge clamp diverts the current to ground.

6.3.2 IEC 61000-4-4 EFT Protection

The I/O pins can withstand an electrical fast transient burst of up to 80 A (5/50 ns waveform, 4 kV with $50-\Omega$ impedance). An ESD-surge clamp diverts the current to ground.

6.3.3 IEC 61000-4-5 Surge Protection

The I/O pins can withstand surge events up to 4.5 A and 67W (8/20 µs waveform). An ESD-surge clamp diverts this current to ground.

6.3.4 IO Capacitance

The capacitance between each I/O pin to ground is 0.77 pF (typical) and 0.95 pF (maximum).

6.3.5 DC Breakdown Voltage

The DC breakdown voltage of each I/O pin is ±8.3 V typical. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of ±5.5 V.

6.3.6 Low Leakage Current

The I/O pins feature an low leakage current of 10 nA (maximum) with a bias of ±2.5 V.

6.3.7 Low ESD Clamping Voltage

The I/O pins feature an ESD clamp that is capable of clamping the voltage to 24 V (TLP I_{PP} = 16 A).

6.3.8 Industrial Temperature Range

This device features an industrial operating range of -40°C to +125°C.

6.3.9 Industry Standard Footprint

The layout of this device makes it simple and easy to add protection to an existing layout. The packages offers flow-through routing, requiring minimal modification to an existing layout.

6.4 Device Functional Modes

The ESD401 is a passive integrated circuit that triggers when voltages are above V_{BRF} or below V_{BRR} . During ESD events, voltages as high as ± 24 kV (contact) or ± 30 kV (air) can be directed to ground via the internal diode network. When the voltages on the protected line fall below the trigger levels of ESD401 (usually within 10s of nano-seconds) the device reverts to passive.

Product Folder Links: ESD401

Figure 6-1 shows typical TLP behavior of bi-directional ESD device that does not exhibit snapback.

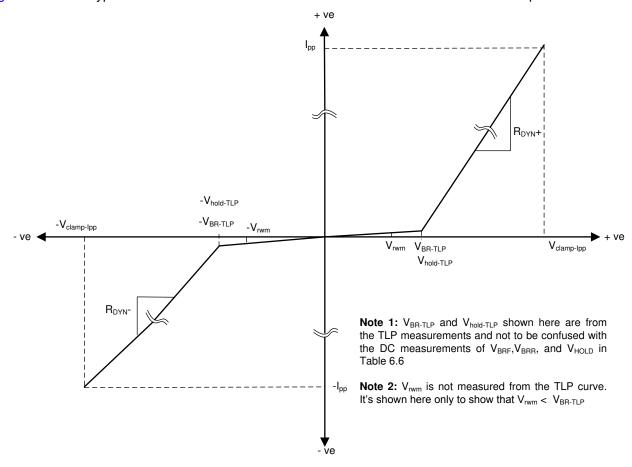


Figure 6-1. Typical TIpLP Behavior Of Bi-directional ESD Device that Does Not Exhibit Snapback

7 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

The ESD401 is a diode type TVS which is used to provide a path to ground for dissipating ESD events on high-speed signal lines between a human interface connector and a system. As the current from ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low R_{DYN} of the triggered TVS holds this voltage, V_{CLAMP} , to a safe level for the protected IC.

7.2 Typical Application

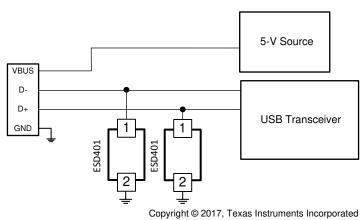


Figure 7-1. USB 2.0 ESD Schematic

7.2.1 Design Requirements

For this design example, two ESD401 devices are being used in a USB 2.0 application. This provides a complete ESD protection scheme.

Given the USB 2.0 application, the parameters listed in Table 7-1 are known.

Table 7-1. Design Parameters

DESIGN PARAMETER	VALUE
Signal range on DP-DM lines	0 V to 3.6 V
Operating frequency on DP-DM lines	up to 240 MHz or 480 Mbps

7.2.2 Detailed Design Procedure

7.2.2.1 Signal Range

The ESD401 supports signal ranges between –5.5 V and 5.5 V, which supports the USB 2.0 signal range of 0 to 3.6 V on the DM/DP lines..

7.2.2.2 Operating Frequency

The ESD401 has a 0.85 pF (typical) capacitance, which supports the USB 2.0 data rates of 480 Mbps.

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7.2.3 Application Curves

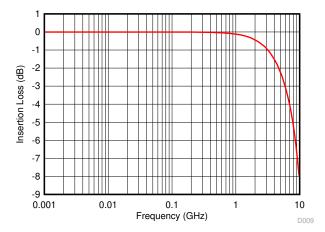


Figure 7-2. Insertion Loss

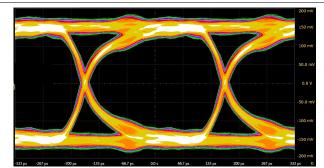


Figure 7-3. Eye Diagram - 3-Gbps Signal No Device

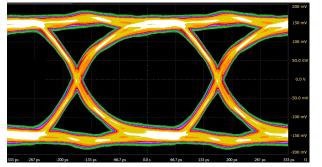


Figure 7-4. Eye Diagram - 3-Gbps Signal With ESD401

7.3 Power Supply Recommendations

The ESD401 is a passive ESD device so there is no need to power it. Take care not to violate the recommended I/O specification (–5.5 V to 5.5 V) to ensure the device functions properly.

7.4 Layout

7.4.1 Layout Guidelines

- The optimum placement is as close to the connector as possible.
 - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
 - The PCB designer must minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
 - Electric fields tend to build up on corners, increasing EMI coupling.



7.4.2 Layout Example

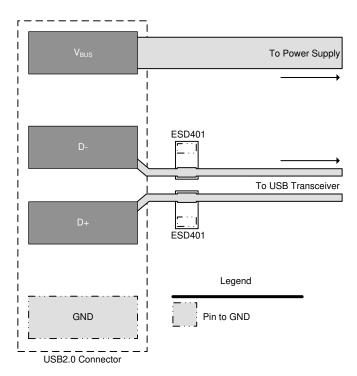


Figure 7-5. USB 2.0 ESD Layout



8 Device and Documentation Support

8.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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8.3 Trademarks

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8.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

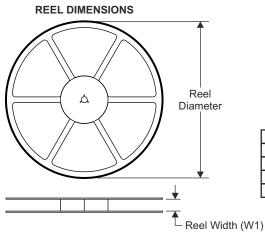
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Page
6

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



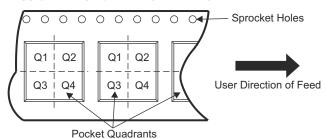
10.1 Tape and Reel Information



TAPE DIMENSIONS K0 P1 B0 W Cavity A0

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

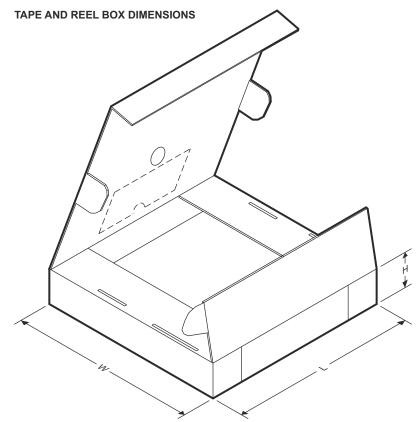


Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ESD401DPYR	X1SON	DPY	2	10,000	180.00	8.400	0.67	1.15	0.46	2.0	8.000	Q2

Product Folder Links: ESD401

14





Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ESD401DPYR	X1SON	DPY	2	10,000	185.000	210.000	35.000

DPY0002A

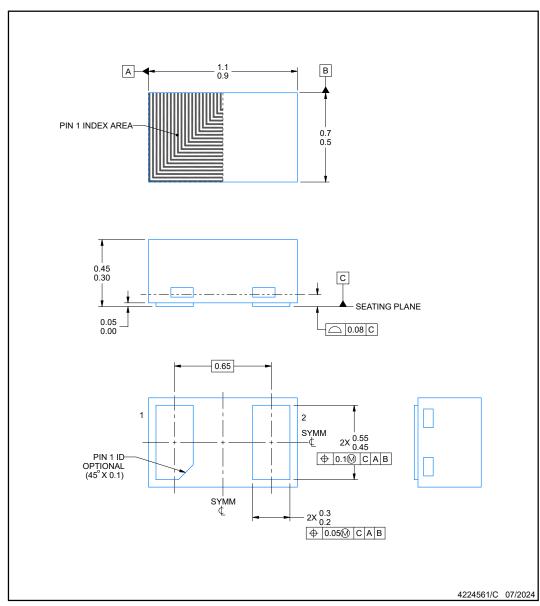


11 Mechanical Data

PACKAGE OUTLINE

X1SON - 0.45 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M
 This drawing is subject to change without notice.



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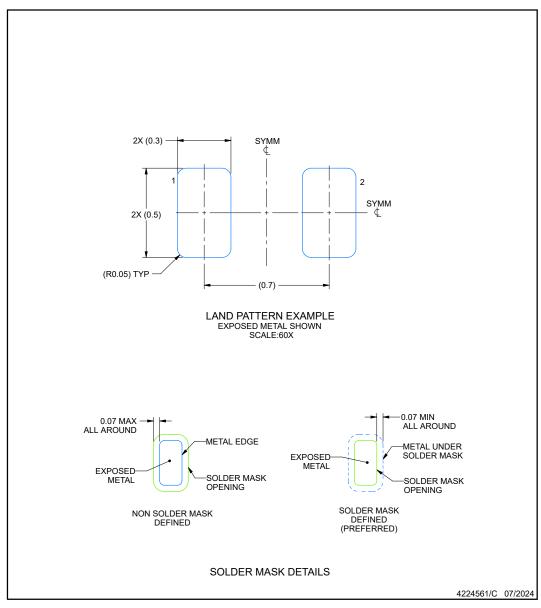


EXAMPLE BOARD LAYOUT

DPY0002A

X1SON - 0.45 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

- 3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 4. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



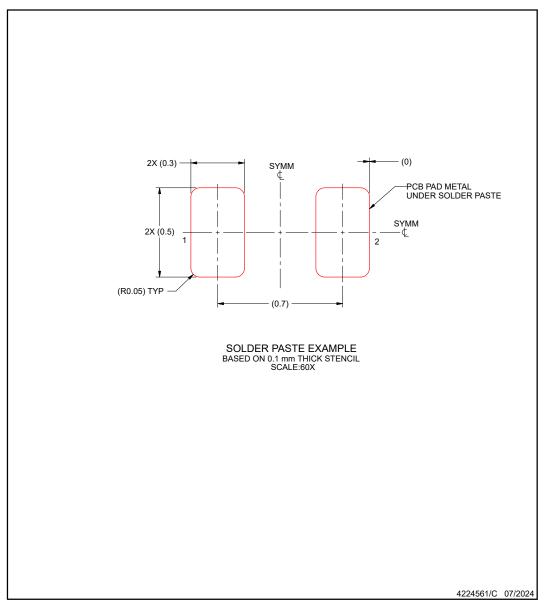


EXAMPLE STENCIL DESIGN

DPY0002A

X1SON - 0.45 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
ESD401DPYR	ACTIVE	X1SON	DPY	2	10000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	81	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

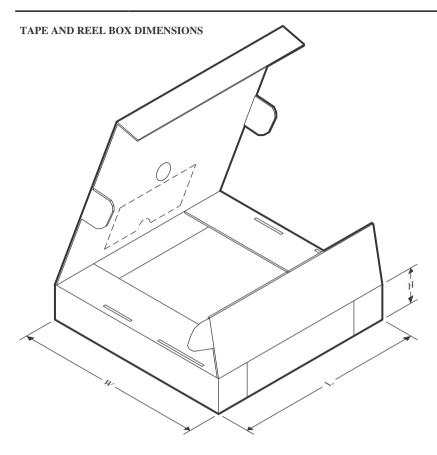


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ESD401DPYR	X1SON	DPY	2	10000	180.0	8.4	0.67	1.15	0.46	2.0	8.0	Q2

PACKAGE MATERIALS INFORMATION

www.ti.com 25-Sep-2024

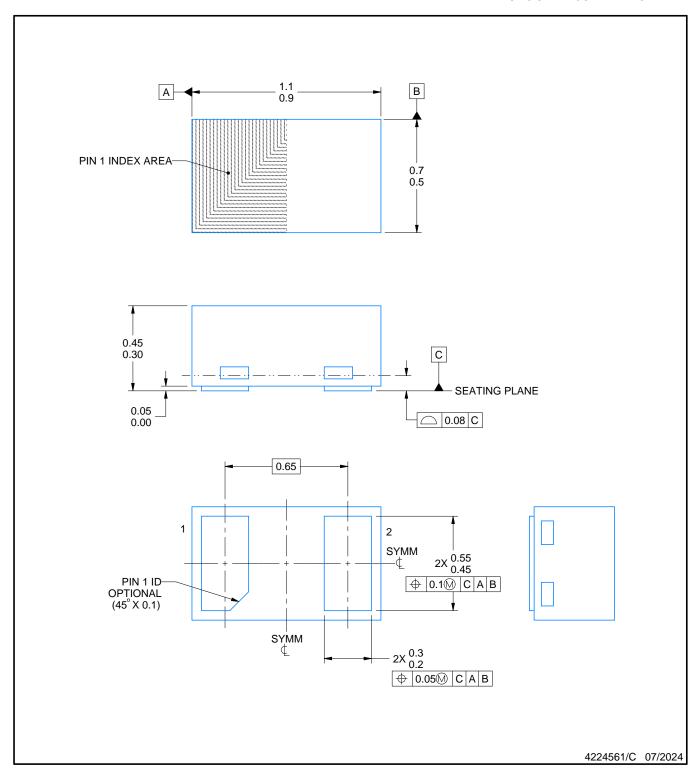


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ESD401DPYR	X1SON	DPY	2	10000	210.0	185.0	35.0



PLASTIC SMALL OUTLINE - NO LEAD

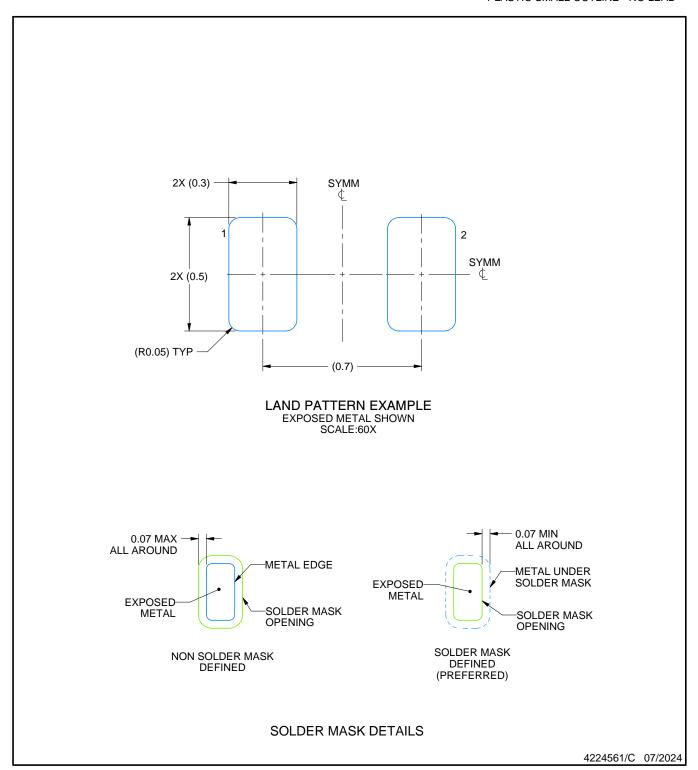


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M
- per ASME Y14.5M
 2. This drawing is subject to change without notice.



PLASTIC SMALL OUTLINE - NO LEAD

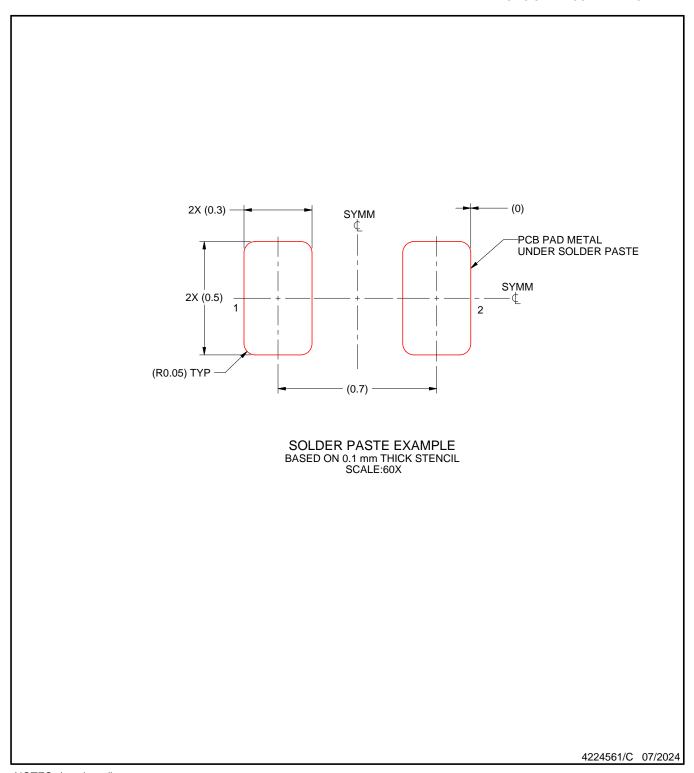


NOTES: (continued)

- 3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).4. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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